

SLPS440 - JUNE 2013

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# 60-V, N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD18532NQ5B

## **FEATURES**

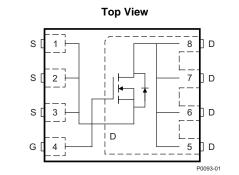
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

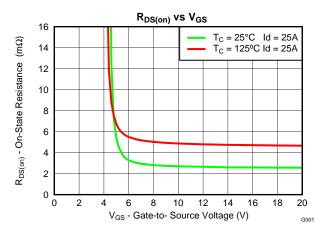
### **APPLICATIONS**

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Isolated Converter Primary Side Switch
- Motor Control

## DESCRIPTION

The NexFET<sup>™</sup> power MOSFET has been designed to minimize losses in power conversion applications.





#### PRODUCT SUMMARY

$T_A = 25^{\circ}$	С	TYPICAL VA	UNIT		
V <sub>DS</sub>	Drain to Source Voltage		V		
Qg	Gate Charge Total (10V) 49				
Q <sub>gd</sub>	Gate Charge Gate to Drain	7.9	nC		
Р	Drain to Source On Resistance	$V_{GS} = 6V$	3.5	mΩ	
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 10V 2.7		mΩ	
V <sub>GS(th)</sub>	Threshold Voltage	2.8		V	

#### **ORDERING INFORMATION**

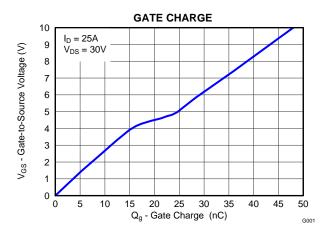
Device	Package	Media	Qty	Ship
CSD18532NQ5B	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

$T_A = 2$	5°C	VALUE	UNIT
V <sub>DS</sub>	Drain to Source Voltage	60	V
$V_{GS}$	Gate to Source Voltage	±20	V
	Continuous Drain Current (Package limited), $T_C = 25^{\circ}C$	100	
ID	Continuous Drain Current (Silicon limited), $T_{C} = 25^{\circ}C$	163	A
	Continuous Drain Current, $T_A = 25^{\circ}C^{(1)}$	22	
I <sub>DM</sub>	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	135	А
PD	Power Dissipation <sup>(1)</sup>	3.2	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D = 85A$ , L = 0.1mH, $R_G = 25\Omega$	360	mJ

(1) Typical  $R_{\theta JA}$  = 40°C/W on a 1-inch² , 2-oz. Cu pad on a 0.06-inch thick FR4 PCB.

(2) Pulse duration  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$ 



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

### (T<sub>A</sub> = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
Static Ch	naracteristics	· ·	L.		
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	60		V
I <sub>DSS</sub>	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 48V$		1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = 20V$		100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.4 2.8	3.4	V
Р	Drain to Source On Resistance	$V_{GS} = 6V, I_D = 25A$	3.5	4.4	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 25A$	2.7	3.4	mΩ
g <sub>fs</sub>	Transconductance	$V_{DS} = 30V, I_{D} = 25A$	140		S
Dynamic	Characteristics				
C <sub>iss</sub>	Input Capacitance		4100	5340	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0V$ , $V_{DS} = 30V$ , $f = 1MHz$	495	644	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		16	21	pF
R <sub>G</sub>	Series Gate Resistance		1.2	2.4	Ω
Qg	Gate Charge Total (10V)	$V_{DS} = 30V, I_D = 25A$	49	64	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain		7.9		nC
Q <sub>gs</sub>	Gate Charge Gate to Source		16		nC
Q <sub>g(th)</sub>	Gate Charge at Vth		11		nC
Q <sub>oss</sub>	Output Charge	$V_{DS} = 30V, V_{GS} = 0V$	69		nC
t <sub>d(on)</sub>	Turn On Delay Time		8.2		ns
tr	Rise Time	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 10V,	8.7		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_{DS} = 25A, R_G = 0\Omega$	20		ns
t <sub>f</sub>	Fall Time		2.7		ns
Diode Cl	haracteristics				
V <sub>SD</sub>	Diode Forward Voltage	$I_{SD} = 25A, V_{GS} = 0V$	0.8	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{DS} = 30V, I_{F} = 25A,$	139		nC
t <sub>rr</sub>	Reverse Recovery Time	di/dt = 300A/µs	64		ns

## THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{ extsf{ heta}JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			0.8	°C/W
$R_{\thetaJA}$	Thermal Resistance Junction to Ambient <sup>(1)(2)</sup>			50	°C/W

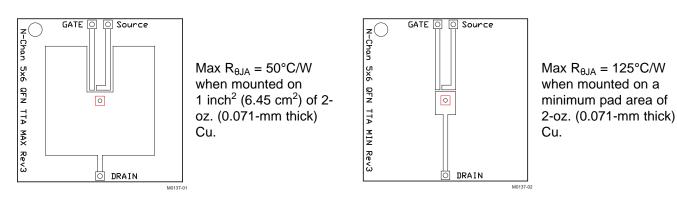
 $R_{\theta,JC}$  is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB.  $R_{\theta,JC}$  is specified by design, whereas  $R_{\theta,JA}$  is determined by the user's board design. Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu. (1)

(2)

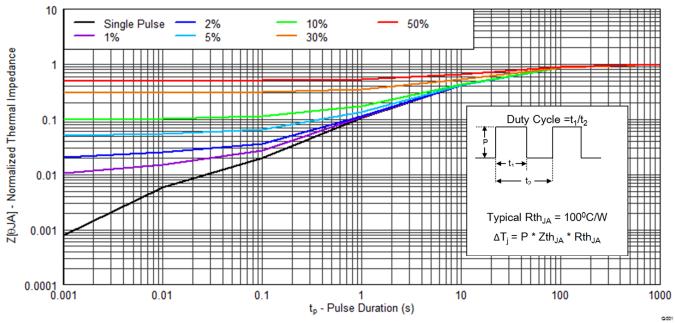


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## **TYPICAL MOSFET CHARACTERISTICS**



 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

Figure 1. Transient Thermal Impedance

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 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

### **TYPICAL MOSFET CHARACTERISTICS (continued)**

200 200  $V_{DS} = 5V$ 180 180 I<sub>DS</sub> - Drain-to-Source Current (A) € 160 160 I<sub>DS</sub> - Drain-to-Source Current 140 140 120 120 100 100 80 80 60 60 T<sub>C</sub> = 125°C  $V_{GS} = 10V$ 40 40  $T_C = 25^{\circ}C$  $V_{GS} = 8V$ 20 20  $V_{GS} = 6V$  $T_C = -55^{\circ}C$ 0 0 0.1 0.3 0.4 0.5 0.7 2 5 7 0 0.2 0.6 0.8 0 3 4 6 8 V<sub>DS</sub> - Drain-to-Source Voltage (V) V<sub>GS</sub> - Gate-to-Source Voltage (V) G001 G00<sup>-</sup> **Figure 2. Saturation Characteristics Figure 3. Transfer Characteristics** 10 100000  $I_D = 25A$  $C_{iss} = C_{gd} + C_{gs}$ 9 V<sub>GS</sub> - Gate-to-Source Voltage (V)  $C_{oss} = C_{ds} +$  $V_{DS} = 30V$ 8  $C_{rss} = C_{qd}$ 10000 C - Capacitance (pF) 7 6 5 1000 4 3 100 2 1 0 10 5 10 15 20 25 30 35 45 10 40 0 20 0 50 30 Q<sub>q</sub> - Gate Charge (nC) V<sub>DS</sub> - Drain-to-Source Voltage (V) G001 G001 Figure 4. Gate Charge Figure 5. Capacitance 3.4 16  $T_C = 25^{\circ}C$  Id = 25A  $I_D = 250 uA$  $R_{DS(on)}$  - On-State Resistance  $\left(m\Omega\right)$ 3.2 14  $T_{C} = 125^{\circ}C \text{ Id} = 25A$ V<sub>GS(th)</sub> - Threshold Voltage (V) 3 12 2.8 10 2.6 8 2.4 6 2.2 4 2 2 1.8 **–** –75 0 -25 25 75 125 175 0 2 4 6 8 10 12 14 16 18 20 T<sub>C</sub> - Case Temperature (°C) V<sub>GS</sub> - Gate-to- Source Voltage (V) G001 G001 Figure 6. Threshold Voltage vs. Temperature Figure 7. On-State Resistance vs. Gate-to-Source Voltage

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#### **TYPICAL MOSFET CHARACTERISTICS (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

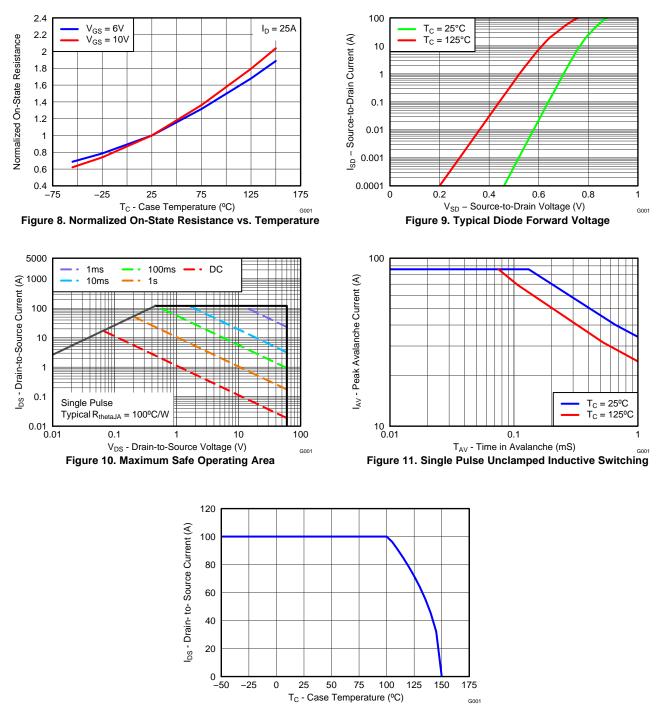


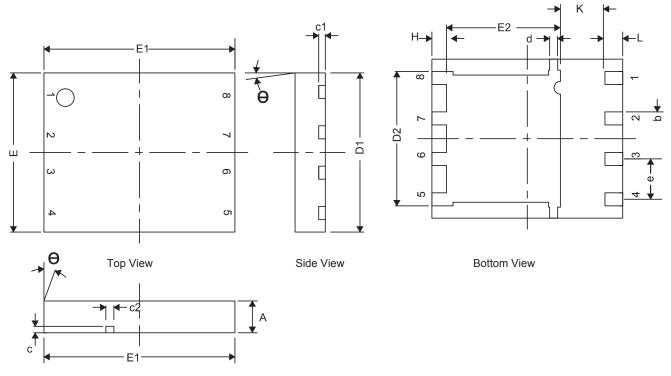
Figure 12. Maximum Drain Current vs. Temperature

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MECHANICAL DATA

## **Q5B Package Dimensions**



Front View

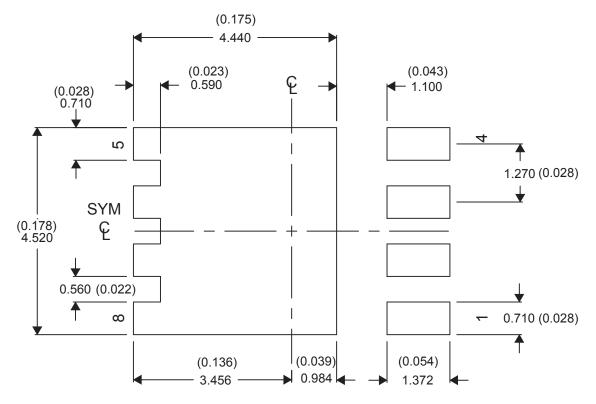
DIM		MILLIMETERS						
DIW	MIN	NOM	MAX					
А	0.80	1.00	1.05					
b	0.36	0.41	0.46					
С	0.15	0.20	0.25					
c1	0.15	0.20	0.25					
c2	0.20	0.25	0.30					
D1	4.90	5.00	5.10					
D2	4.12	4.22	4.32					
d	0.20	0.25	0.30					
E	4.90	5.00	5.10					
E1	5.90	6.00	6.10					
E2	3.48	3.58	3.68					
е		1.27 TYP						
L	0.46	0.56	0.66					
θ	0°							
К	1.40 TYP							



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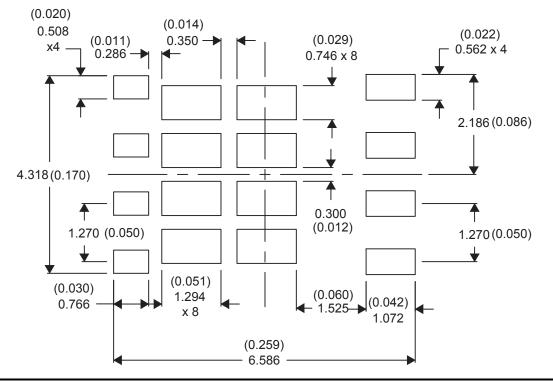
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#### **Recommended PCB Pattern**



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

#### **Recommended Stencil Pattern**

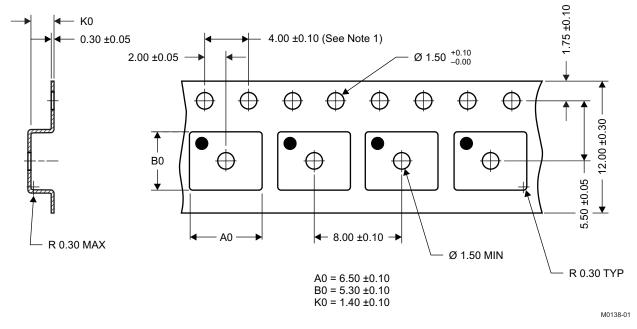


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### **Q5B Tape and Reel Information**



#### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket



27-Jun-2013

## PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
CSD18532NQ5B	ACTIVE	VSON	DNK	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	18532N	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

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<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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